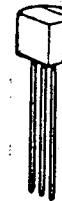




**MICRO ELECTRONICS**

CASE TO-92A

MPS-D04 (NPN) and MPS-D54 (PNP) are complementary darlington silicon planar transistors designed for use in high gain driver applications.



EBC

**ABSOLUTE MAXIMUM RATINGS** For p-n-p devices, voltage and current values are negative.

Collector-Emitter Voltage	V <sub>CES</sub>	25V
Emitter-Base Voltage	V <sub>EBO</sub>	10V
Collector Current	I <sub>C</sub>	300mA
Total Power Dissipation @ T <sub>A</sub> =25°C	P <sub>tot</sub>	625mW
@ T <sub>C</sub> =25°C		1.5W
Operating Junction & Storage Temperature	T <sub>j</sub> , T <sub>stg</sub>	-55 to +150°C

**ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C)**

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	BV <sub>CES</sub>	25		V	I <sub>C</sub> =100μA V <sub>BE</sub> =0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	10		V	I <sub>E</sub> =10μA I <sub>C</sub> =0
Collector Cutoff Current	I <sub>CES</sub>		1	μA	V <sub>CE</sub> =20V V <sub>BE</sub> =0
Collector Cutoff Current	I <sub>CBO</sub>		1	μA	V <sub>CB</sub> =20V I <sub>E</sub> =0
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>		1	V	I <sub>C</sub> =100mA I <sub>B</sub> =0.1mA
D.C. Current Gain	H <sub>FE</sub> *	1000			I <sub>C</sub> =10mA V <sub>CE</sub> =5V
		2000			I <sub>C</sub> =100mA V <sub>CE</sub> =5V
		1000			I <sub>C</sub> =300mA V <sub>CE</sub> =5V
Current Gain-Bandwidth Product	f <sub>T</sub>	100		MHz	I <sub>C</sub> =10mA V <sub>CE</sub> =5V f=100MHz

\* Pulse Test : Pulse Width=0.3ms, Duty Cycle=1%

**MICRO ELECTRONICS LTD.**

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